

**IN THE CLAIMS:**

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please CANCEL claim 1 and ADD claims 11-23 in accordance with the following:

1-10 Canceled

11. (new) A circuit device provided on a substrate and comprising:  
a semiconductor component arranged on the substrate and having an electrical contact surface ;and

at least one connection line on the substrate to contact with the contact surface of the semiconductor component,

wherein

the electrical connection line is part of at least one discrete passive electrical component arranged on the substrate.

12. (new) The circuit device in accordance with claim 11, wherein  
the discrete passive electrical component is a capacitor, and  
the electrical connection line is an electrode of the capacitor.

13. (new) The circuit arrangement in accordance with claim 11, wherein  
the discrete passive electrical component is a coil , and  
the electrical connection line is a winding of the coil.

14. (new) The circuit device in accordance with claim 11, wherein  
the discrete passive electrical component is an electrical resistor , and  
the electrical connection line is a wire resistor.

15. (new) The circuit device in accordance with claim 11, wherein the discrete passive electrical component is a part of a sensor of a physical variable.

16. (new) The circuit arrangement in accordance with claim 11, wherein the semiconductor component is a power semiconductor component.
17. (new) The circuit device in accordance with claim 16, wherein the power semiconductor component is selected from the group consisting of MOSFETs, IGBTs and bipolar transistors.
18. (new) The circuit device in accordance with claim 14, wherein the discrete passive electrical component is a part of a sensor of a physical variable.
19. (new) The circuit arrangement in accordance with claim 18, wherein the semiconductor component is a power semiconductor component.
20. (new) The circuit device in accordance with claim 19, wherein the power semiconductor component is selected from the group consisting of MOSFETs, IGBTs and bipolar transistors.
21. (new) A method for producing a circuit device, comprising:  
producing a semiconductor component on a substrate, the semiconductor component having an electrical contact surface facing away from the substrate; and  
producing an electrical connection line that contacts the contact surface of the semiconductor component, the electrical connection line being part of a discrete passive electrical component.
22. (new) The method in accordance with claim 21, wherein  
the electrical connection line contacts the contact surface at an electrical contact, the electrical contact faces away from the substrate, and  
a layer of electrically insulating material is provided on the semiconductor component and the substrate in such a way that the electrical contact is exposed.
23. (new) The method in accordance with claim 22, wherein a complete layer of electrically insulating material is first applied, and then the electrical contact is exposed by opening a window in the electrically insulating material.